



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

SOT-323 Plastic-Encapsulate Diode

RB706F-40 SCHOTTKY BARRIER DIODE

FEATURES

Power dissipation

P_D : 200 mW ($T_{amb}=25^{\circ}C$)

Collector current

I_F : 30 mA

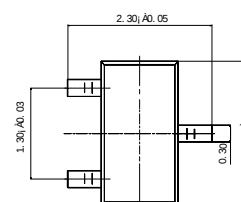
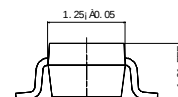
Collector-base voltage

V_R : 40 V

Operating and storage junction temperature range

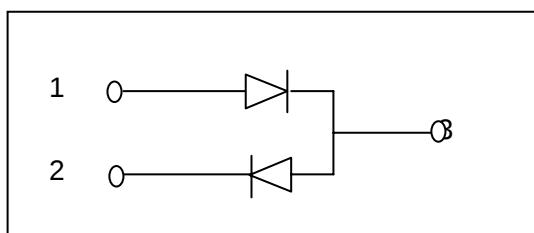
T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$

SOT-323



Unit: mm

CIRCUIT:



MARKING: 3J

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)}$	$I_R=100\mu A$	40		V
Reverse voltage leakage current	I_R	$V_R=10V$		1	μA
Forward voltage	V_F	$I_F=1mA$		0.37	V
Diode capacitance	C_D	$V_R=1V, f=1MHz$		5	pF